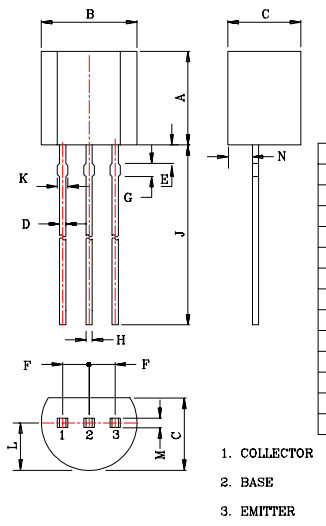
BC559/560

EPITAXIAL PLANAR PNP TRANSISTOR

LOW NOISE APPLICATION.

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	BC559	V_{CBO}	-30	V
	BC560		-50	
Collector-Emitter Voltage	BC559	V_{CEO}	-30	V
	BC560		-45	
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		I_C	-100	mA
Collector Power Dissipation		P_C	625	mW
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55~150	℃



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

TO-92

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	BC559	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-30	-	-	V
	BC560			-45	-	-	
Collector-Base Breakdown Voltage	BC559	$V_{(BR)CBO}$	I_C=-10μA, I_E=0	-30	-	-	V
	BC560			-50	-	-	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-5.0	-	-	V
Collector Cut-off Current		I_{CBO}	V_{CB}=-30V, I_E=0	-	-	-15	nA
DC Current Gain		h_{FE}	I_C=-2mA, V_{CE}=-5V	110	-	800	
Base-Emitter Voltage		$V_{BE(ON)}$	I_C=-2mA, V_{CE}=-5V	-0.55	-	-0.7	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=-100mA, I_B=-5mA	-	-	-0.6	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	I_C=-100mA, I_B=-5mA	-	-0.9	-	V
Transition Frequency		f_T	I_C=-10mA, V_{CE}=-5V, f=100MHz	-	300	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	-	7.0	pF
Noise Figure		NF	I_C=-200μA, V_{CE}=-5V Rg=10kΩ, f=1kHz	-	-	4.0	dB

Note : h_{FE} Classification A:110~220 , B:200~450 , C:420~800